

Code: 15EC-21T

Register				
Number				

II Semester Diploma Examination, Nov./Dec. 2016

BASICS OF SEMICONDUCTOR DEVICES

Time: 3 Hours			[Max. Marks : 100			
Note		 (i) Answer any six questions from Part - A. (6 × 5 = 30 (ii) Answer any seven full questions from Part - B. (7 × 				
1.	Defi	PART – A ne Doping. Explain energy band diagram of p-type semions	conductor. 5			
2.	Exp	lain the formation of PNP transistor.	5			
3.	Outl	ine different regions in output characteristics of BJT in C	E mode. BETA CONSOLE!			
4.	Exp	lain the principle of operation of JFET briefly.	Diploma ⁵ [All Branches]			
5.	Wri	te applications of CMOS.	Beta Console Education 3- 5			
6.	List	the features of GUNN diode.	5			
7.	Defi	ine SSI, MSI, LSI, VLSI and ULSI.	Diploma Que S tion Papers [2015-			
8.	List	the applications and advantages of LED.	19] Beta Console Education 5			
9,	Wri	te a short note on opto-coupler.	5			
10.	(a) (b)	PART – B Distinguish between n-type and p-type semiconductors. Explain the behaviour of zener diode under reverse becharacteristic plot.				
11.	(a)	Define: (i) Valence electron (ii) Intrinsic semiconductor (iii) Cut-in voltage (iv) Dopant (v) Reverse saturation current	5			
	(b)	Describe the effect of temperature on Diode Current.	5			
		[1 of 2]	(Turn over			